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Innovative Silicon Inc. named in *EE Times* Silicon 60 Emerging Start-Ups list for Fourth Consecutive Year

SANTA CLARA, Calif., July 17, 2007 — Innovative Silicon Inc. (ISi), the developer of Z-RAM[®] high-density memory intellectual property (IP), has been named for the fourth consecutive year in *EE Times*' latest '60 Emerging Start-ups' list, Version 6.0 – known throughout industry as the 'Silicon 60'. The entire list can be found at <http://eetimes.com/news/semi/showArticle.jhtml?articleID=200001932>.

EETimes' European News Director Peter Clarke, who has been following ISi since the company was founded in 2002 by Doctors Pierre Fazan and Serguei Okhonin, writes: "*EE Times* first published its Emerging Start-ups' list in April 2004. In the current Version 6.0, editors have selected companies based on a mix of criteria including: technology, intended market, maturity, financial position and investment profile. Innovative Silicon Inc. was founded to develop an SOI-based 'floating body' single-transistor memory. Now, ISi has licensed its Z-RAM[®] (Zero Capacitor RAM) memory to Advanced Micro Devices Inc. amongst others."

Commented ISi's Jeff Lewis, VP Marketing: "The elegance of a single-transistor DRAM solution has broad appeal for chip makers requiring the right combination of speed, power

and density. We are delighted that EETimes – the voice of our industry – has included ISi and Z-RAM® in its Silicon 60 list every year since the list's inception.”

About Innovative Silicon

Innovative Silicon Inc. (ISi) delivers ultra-high density memory IP for embedded SoC, MPU and portable consumer applications requiring low power, high density and high speed. Endorsed by IEEE Spectrum Magazine in January 2007 as the ‘winning’ semiconductor technology, and again in April 2007 by winning its ACE award for Emerging Technology, ISi's Z-RAM® memory offers up to twice the density of embedded DRAM and is up to five times denser than embedded SRAM. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. With more than 20 patents already granted, Z-RAM®'s unique single-transistor architecture is the world's lowest cost semiconductor memory solution. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see www.z-ram.com.

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